

ABSTRACT

5 A silicon oxide powder can be continuously prepared by
feeding a raw material powder mixture containing silicon
dioxide powder into a reaction chamber (2) at a temperature
of 1,100-1,600°C, to produce a silicon oxide gas,
transferring the silicon oxide gas to a deposition chamber
(11) through a transfer conduit (10) maintained at a
10 temperature of from higher than 1,000°C to 1,300°C, causing
silicon oxide to deposit on a substrate (13) which is
disposed and cooled in the deposition chamber, scraping the
silicon oxide deposit, and recovering the deposit in a
recovery chamber (18). The method and apparatus is capable
15 of continuous and stable production of amorphous silicon
oxide powder of high purity.

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